

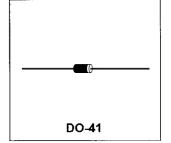
## **Switchmode Power Rectifiers**

... Designed for use in switching power supplies, inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- \* High Surge Capacity
- \* Low Power Loss, High efficiency
  \* Glass Passivated chip junctions
- \* 150 °C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction
- \* Low Forward Voltage, High Current Capability
- \* Utrafast 50 & 75 Nanosecond Recovery Time
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

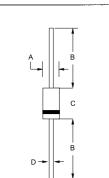
## **ULTRA FAST RECTIFIERS**

1.0 AMPERES 500-1000 VOLTS



## **MAXIMUM RATINGS**

Characteristic	Symbol	SF17	SF18	SF19	SF110	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	500	600	800	1000	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	350	420	560	700	٧
Average Rectifier Forward Current	l <sub>o</sub>	1.0				Α
Non-Repetitive Peak Surge Current ( Surge applied at rate load conditions halfware, single phase, 60Hz )	I <sub>FSM</sub>	25				Α
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 65 to + 150				°C



DIM	MILLMETERS				
	MIN	MAX			
Α	2.00	2.70			
В	25.40				
С	4.10	5.20			
D	0.70	0.90			

## **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	SF17	SF18	SF19	SF110	Unit
Maximum Instantaneous Forward Voltage $(I_F = 1.0 \text{ Amp}, T_C = 25 ^{\circ}\text{C})$	V <sub>F</sub>	1.	50	1.	75	<b>V</b>
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_c = 25$ °C) (Rated DC Voltage, $T_c = 125$ °C)	l <sub>R</sub>	5.0 50				uA
Reverse Recovery Time ( $I_F = 0.5 \text{ A}$ , $I_R = 1.0 \text{ , } I_{rr} = 0.25 \text{ A}$ )	T <sub>rr</sub>	50			75	ns
Typical Junction Capacitance ( Reverse Voltage of 4 volt & f=1 MHz)	C <sub>P</sub>	15		1	10	

CASE---Transfer molded plastic

POLARITY---Cathode indicated polarity band

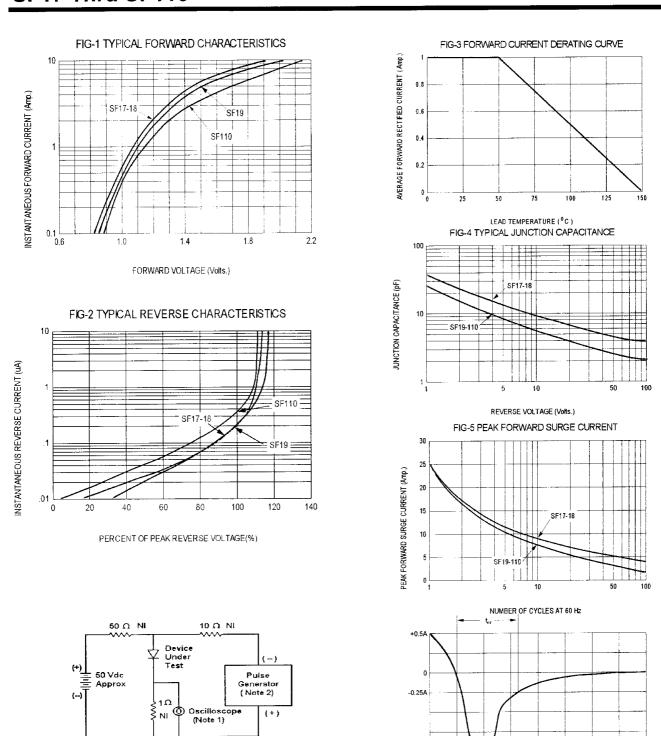


Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram

-1.0A

Set time base for 20 ns/div

Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M  $\Omega$  , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50  $\Omega$ 

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.